16 AMPERES COMPLEMENTARY SILICON-POWER TRANSISTORS 250 VOLTS, 250 WATTS

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TO−204AA (TO−3)
CASE 1−07
STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	250	Vdc
Collector−Base Voltage	V_{CBO}	400	Vdc
Emitter−Base Voltage	V_{EBO}	5	Vdc
Collector−Emitter Voltage − 1.5V	V_{CEX}	400	Vdc
Collector Current − Continuous	I_C	16	Adc
Collector Current − Peak (Note 1)	I_{CM}	30	Adc
Base Current − Continuous	I_B	5	Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 μs, Duty Cycle 10%.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	0.7	°C/W

MARKING DIAGRAM

MJ2119x = Device Code
x = 5 or 6
G = Pb−Free Package
A = Assembly Location
Y = Year
WW = Work Week
MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
MJ21195G	TO−204 (Pb−Free)	100 Units / Tray
MJ21196G	TO−204 (Pb−Free)	100 Units / Tray

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

I_B

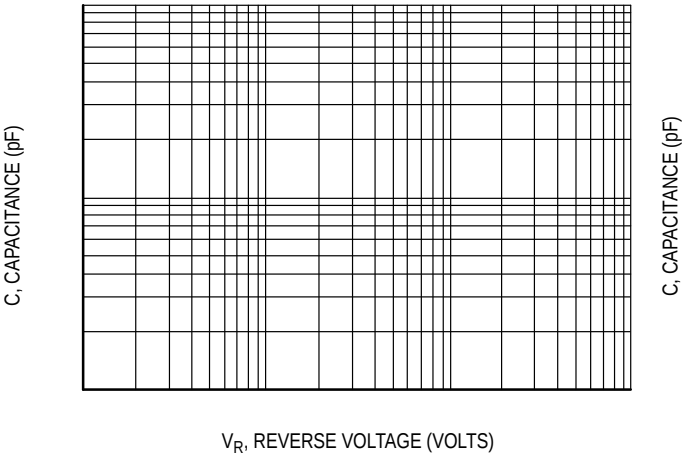


Figure 14. MJ21195 Typical Capacitance

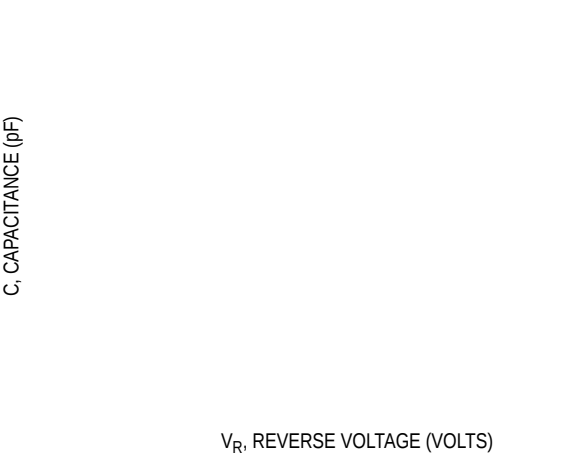
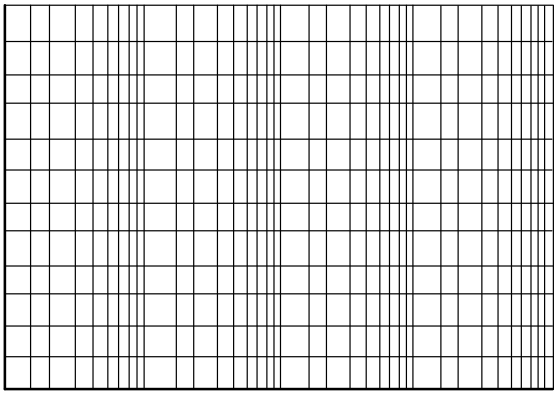
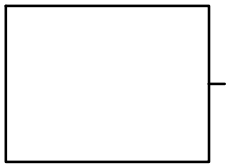
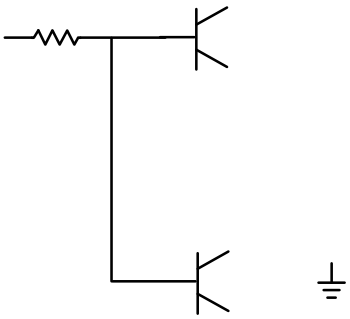
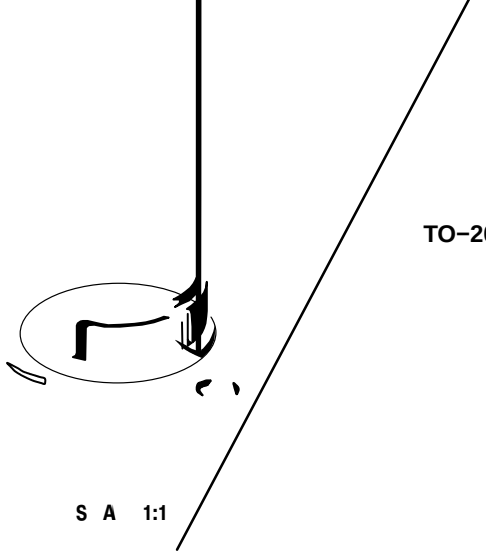


Figure 15. MJ21196 Typical Capacitance









TO−204 (TO−3)

S A 1:1